

TAT2814A

DOCSIS 3.0 / Edge QAM Variable Gain Amplifier

Applications

- Integrated DOCSIS 3.0 / Edge QAM RF Amplifier chain
- Forward path 45 – 1003 MHz variable-gain applications

Product Features

- Meets DOCSIS 3.0 with +4 dB typical performance margin
- < 5 Watt nominal power consumption
- Low-reflection differential input/output stages
- 18 dB typical return loss across entire gain range
- Variable gain attenuator: 18 dB typical range
- 30 dB typical max gain
- +49 dBm typical OIP3
- 2.7 dB typical noise figure
- Typical Input stage bias: 5 V, 290 mA
- Typical Output stage bias: 8 V, 415 mA

General Description

The TAT2814A is an RFIC for DOCSIS 3.0 Output Sections, such as CMTS and Edge QAM. It combines a low-reflection differential input stage, a variable gain step attenuator and an efficient output amplifier to provide significant reduction in power consumption and PC board space. It replaces circuitry requiring up to 10x the board space and 2x the power.

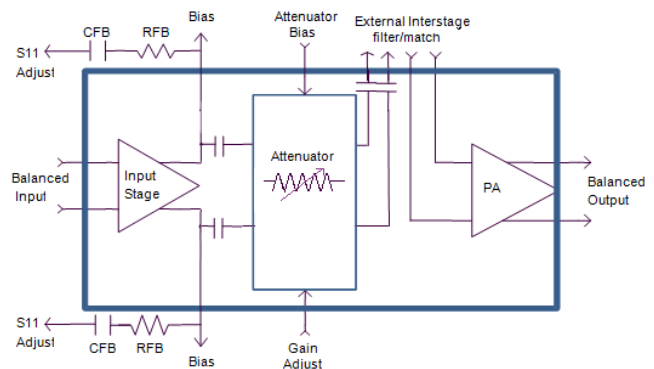
The TAT2814A meets the stringent DOCSIS 3.0 output linearity specifications with extra margin to overcome additional losses before the output connector.

The TAT2814A is packaged in an industry standard 7x7 mm 48-pin QFN and consumes 5 W between a 5 V input amplifier supply and an 8 V output amplifier supply. The TAT2814A utilizes proven GaAs pHEMT to optimize performance and cost. It allows the designer to optimize output stage voltage to significantly reduce power consumption in Edge QAM applications.



48-pin 7x7mm QFN laminate package

Functional Block Diagram



Ordering Information

Part No.	Description
TAT2814A1L	DOCSIS 3.0 Edge QAM Variable Gain Amplifier (lead-free/RoHS compliant 7x7 QFN laminate Pkg)
TAT2814A1L-EB	DOCSIS 3.0 Edge QAM Variable Gain Amplifier Evaluation Board

Standard T/R size = 1000 pieces on a 7" reel.

Specifications

Absolute Maximum Ratings

Parameter ¹	Rating
Storage Temperature	-40 to +100 °C
Device Voltage	+10 V

1. Operation of this device outside the parameter ranges given above may cause permanent damage.
2. T_J for typical V_{DD} = 115 °C.

Recommended Operating Conditions

Parameter	Min	Typ	Max	Units
V _{DD} - stage 1		5		V
V _{PA} - stage 2		8		V
Operating Case Temp	-20		+85	°C
T _J (for >10 ⁶ hours MTTF) ²			150	°C

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

Electrical Specifications

Test conditions unless otherwise noted: ground paddle temp = 25 °C, output stage V_{PA} = +8V, includes input and output balun losses.

Parameter	Conditions	Min	Typical	Max	Units
Operational Frequency Range		45		1003	MHz
Gain at 1003 MHz	See Note 1	27.5	30	32	dB
Gain Variation over Temp	See Note 2		1.25		dB
Gain Flatness	See Note 3		+/- 0.25	± 0.5	dB
Gain Slope	See Note 4	-1.4	-1.0		dB
Attenuator Range	Max Gain - Min Gain		18		dB
Input Return Loss	See Note 1		18		dB
Output Return Loss	See Note 1		20		dB
EQAM Vout	Adjacent ^{5,6}	55.0	56.5		dBmV/ch
Four Channel ACPR on a Single Port	Next-adjacent channel ^{5,7}				
	Third-adjacent channel ^{5,8}				
EQAM Vout	See Notes 5 and 9	63.0	65.0		dBmV
Single Channel Harmonics					
Output P1dB			28		dBm
Output IP3	See Note 10		49		dBm
Noise Figure			2.7		dB
1 st stage current, at 5 V			290	330	mA
2 nd stage current, at 8 V			415	440	mA
Thermal Resistance (junction to case) θ _{jc}			16.8		°C/W

Notes:

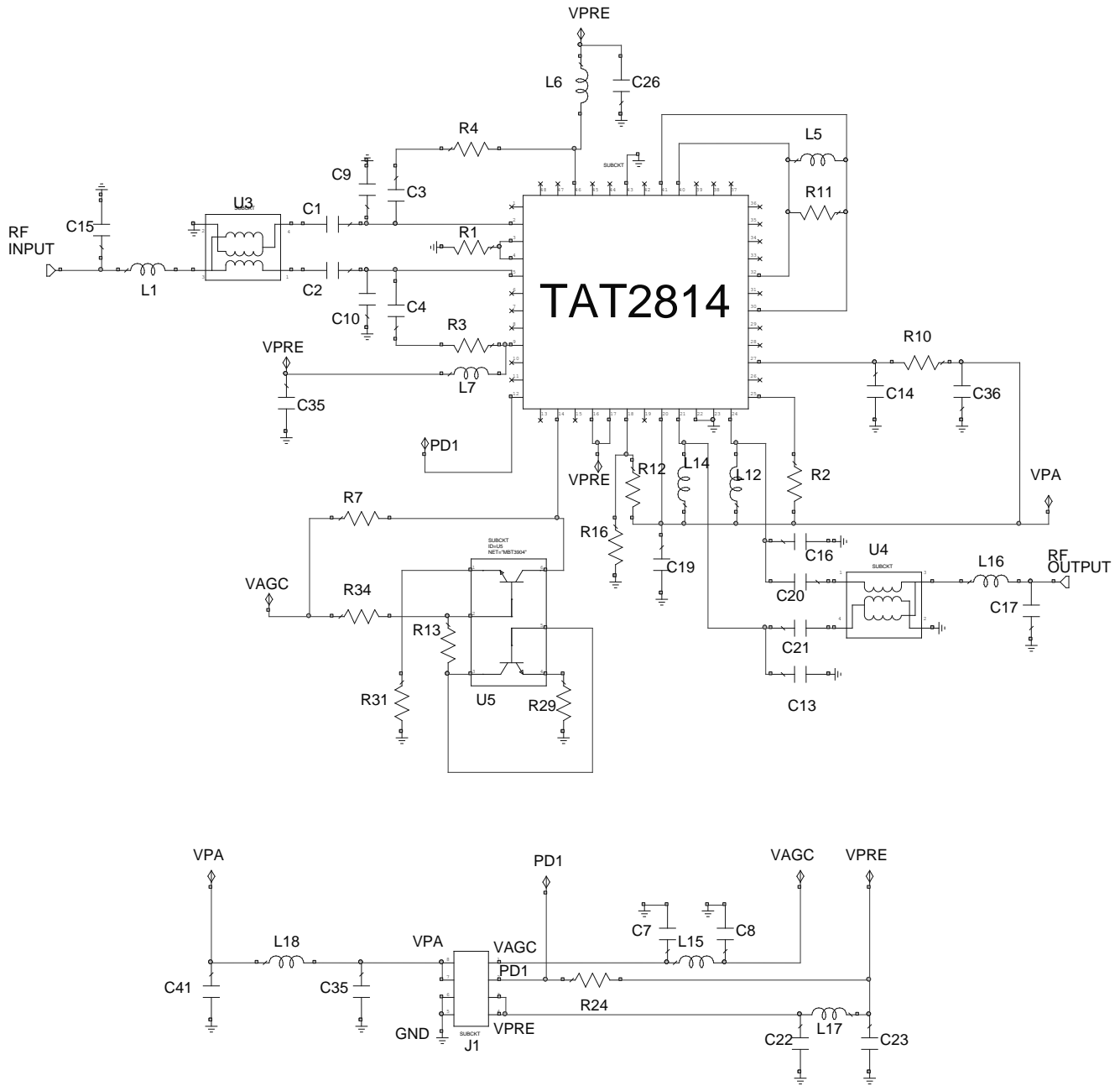
1. I_{AGC} set to 1 mA.
2. Maximum gain deviation within passband with ground paddle temp. range of -20°C to +85°C relative to +45°C.
3. Peak deviation from straight line across full band.
4. Max slope of best fit straight line over all attenuator settings.
5. Production tested at 66 MHz, 330 MHz, and 990 MHz.
6. Adjacent channel (750 kHz from channel block edge to 6 MHz from channel block edge) better than -60 dBc.
7. Next-adjacent channel (6 MHz from channel block edge to 12 MHz from channel block edge) better than -63 dBc.
8. Third-adjacent channel (12 MHz from channel block edge to 18 MHz from channel block edge) better than -65 dBc.
9. In each of 2N contiguous 6 MHz channels or in each of 3N contiguous 6 MHz channels coinciding with 2nd harmonic and with 3rd harmonic components, respectively (up to 1002 MHz) better than -63 dBc.
10. 150 MHz tone spacing at 8 dBm/tone.

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Application Circuit 45-1003 MHz

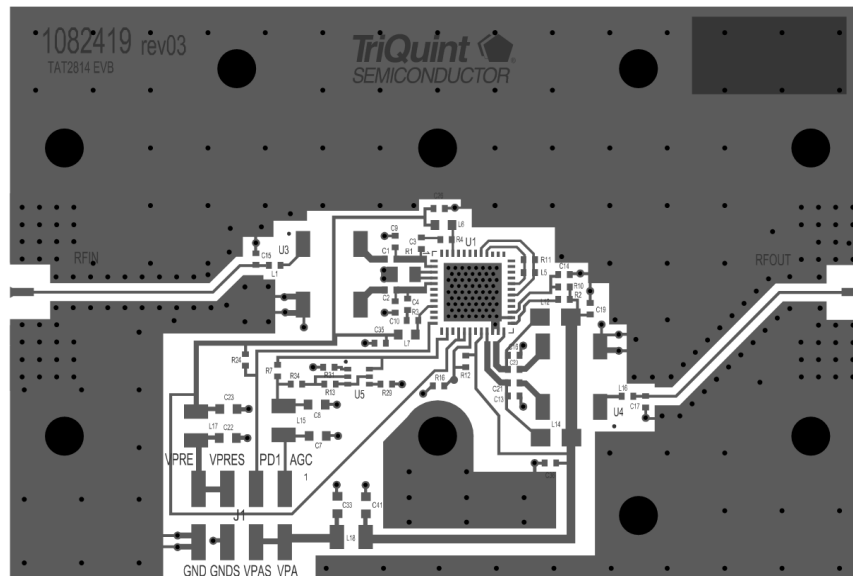


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Layout Drawing



Bill of Material

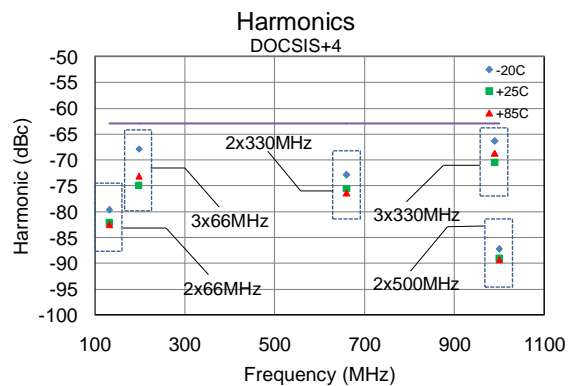
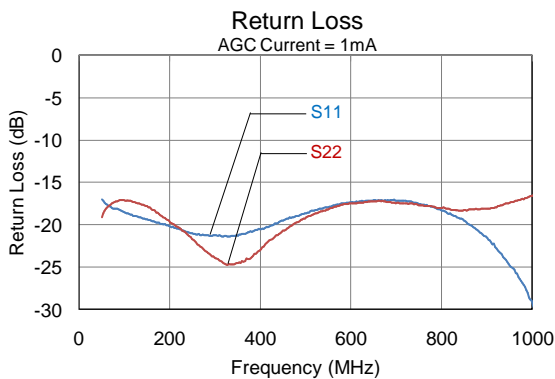
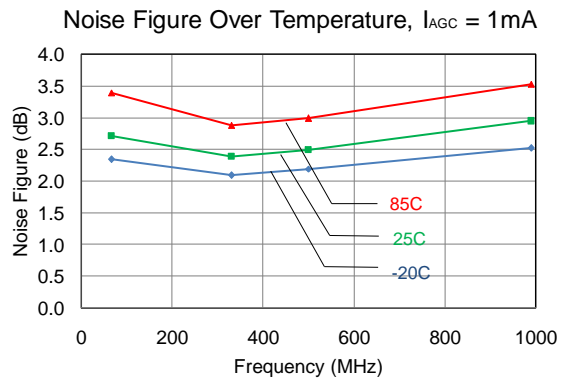
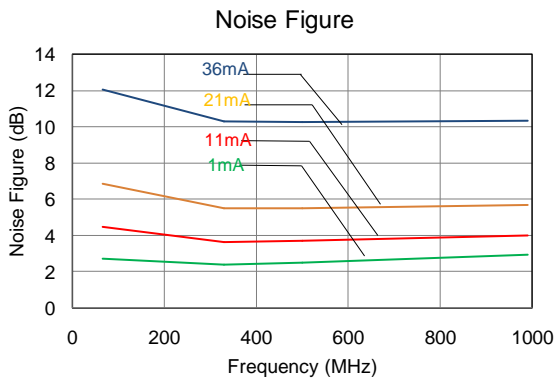
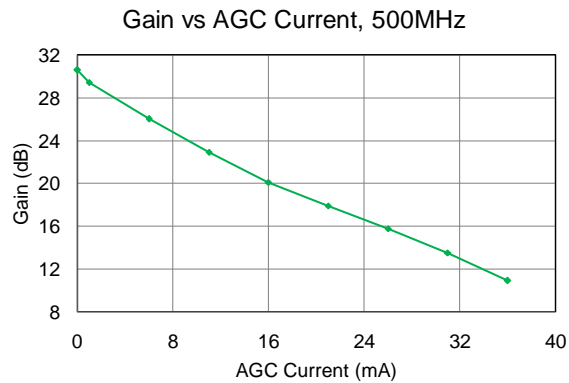
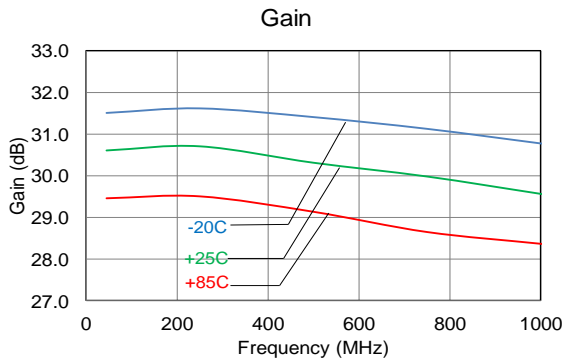
Ref Des	Value	Description	Manufacturer	Part Number
U1		Variable Gain Amplifier, QFN 7x7	TriQuint	TAT2814A
C1, C2, C20, C21	0.01 uF	Ceramic Cap, 0402, X7R, 16V, 10%	Various	
C3, C4, C19, C26, C35	1000 pF	Ceramic Cap, 0402, 5%	Various	
C7, C8, C22, C23, C35, C41	0.01 uF	Ceramic Cap, 0603, X7R, 50V,5%	Various	
C9, C10, C13, C14, C15, C16, C17, R7, R10, R12	DNP	No Load Parts		
L1	1.8 nH	Ind, wirewound, 0402, 5%	Various	
L16, R2, R13	0 Ω	Res, thin film, 0402	Various	
L5	420 nH	Ind, wirewound, 0402, 5%	Coilcraft	0402AF-421XJLU
L6, L7	560 nH	Ind, wirewound, 0603, 5%	Coilcraft	0603AF-561XJRU
L12, L14	500 nH	Ind, wirewound, 1206, 5%	Murata	LQH31HNR50K
L15, L17, L18	0.9 uH	Ind, Ferrite, 1008, 10%	Various	
R1	1.8 Ω	Res, thin film, 0805, 1/4 W 5%	Various	
R3, R4	2.5 kΩ	Res, thin film, 0402, 5%	Various	
R11	560 Ω	Res, thin film, 0402, 5%	Various	
R16	12 kΩ	Res, thin film, 0402, 5%	Various	
R29	36 Ω	Res, thin film, 0402, 5%	Various	
R31	1.0 Ω	Res, thin film, 0402, 5%	Various	
R34	1.27 kΩ	Res, thin film, 0402, 5%	Various	
U3, U4	1:1	Transformer, 50-1200 MHz	M/A-COM	MABA-009210-CT1760
U5	NPN	Trans, dual NPN, SOT363	Various	

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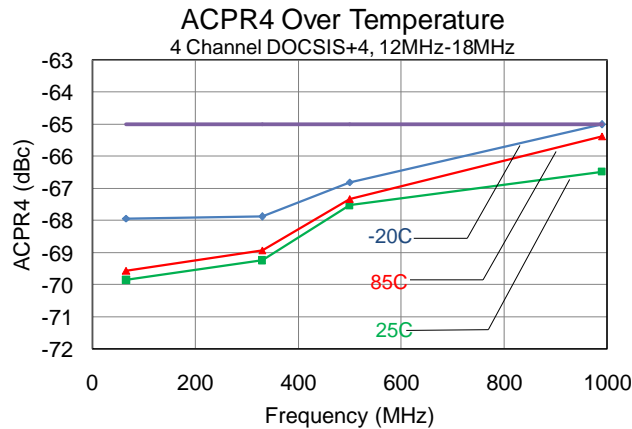
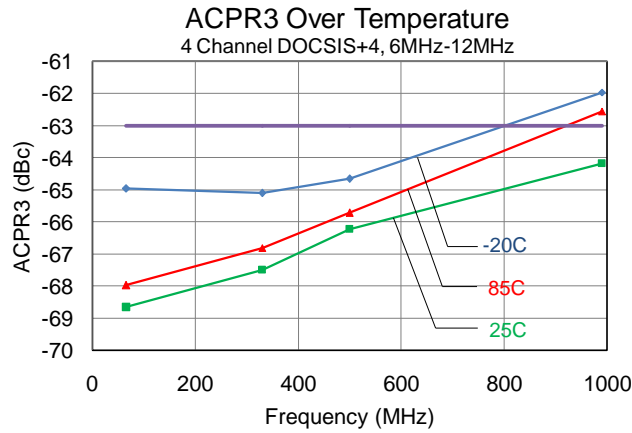
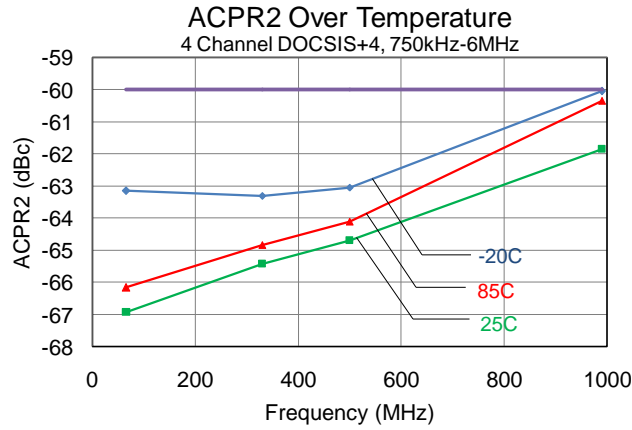
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Typical Performance 40-1000 MHz



Typical Performance 40-1000 MHz (continued)



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Detailed Device Description

Balance

The TAT2814A is designed for excellent differential-mode performance throughout the chain. Unlike many commercially available push-pull amplifiers built with 2 discrete die, both stages of the TAT2814A are single-chip designs utilizing a differential pair topology for best common-mode performance. Provision is made for using external bias inductors to increase tail impedances in the input differential pairs, improving further the signal balance and 2nd order performance through the chain. The RF output of the first stage is connected internally to the differential attenuator and brought out to external pins for applying stage bias and enabling RF feedback to the input. The attenuator outputs are brought out to a single side of the TAT2814A for customers desiring to perform inter-stage filtering or signal processing. The differential inputs to the output stage are located on an adjacent side of the die, spaced to minimize package coupling so as to not limit the performance of off-stage filtering.

Input Matching

The input stage is designed to have 75 Ω differential impedance. However, provision is made for shunt feedback to be easily applied to lower the input impedance to best match to 50 Ω . The external shunt feedback easily allows customers to optimize the input impedance to control DAC anomalies. The bias current of the input stage may be adjusted with an external resistor to ground.

Pre-Amp Powerdown

The preamp stage of the TAT2814A can be powered down by setting PD pin to Logic LOW. V_{DD} pins should be set to 5 V in both power-down and operating modes.

Gain Adjustment

A fully differential gain control function is implemented with a low distortion analog diode-based attenuator. The attenuator provides for monotonic gain adjustment over a full 19 dB attenuation range. The excellent RF match characteristics ensure excellent gain flatness and return loss over the full attenuation range. Control is provided by a single current controlled line. Attenuation is monotonic and linear with control current.

Output Stage

A differential output stage has excellent output linearity performance at very low power. The differential outputs of the second stage may be combined with a commercially available balun to provide for single-ended drive signals. For best performance the bias current of the output stage may be placed in active bias control. This is implemented by sensing the voltage at pin 19 and providing a feedback voltage bias to pin 27. Please contact TriQuint for further details.

Thermal Management

Total power consumption of the TAT2814A is less than 5 Watts. Care must be taken in the layout to provide adequate thermal path with multiple vias under the TAT2814A. A heat sink should also be used to carry heat away from the backside PCB.

Technology

The TAT2814A utilizes proven pHEMT device technology that has yielded over 200 million RFICs to date. For detailed qualification and reliability reports on other products fabricated in this process, please consult TriQuint. Key RFICs that will be used in the TAT2814A have already exceeded industry qualification requirements in other packages.

Bias Current Set

Bias current to each amplification stage is set by external circuitry to allow trade-off of power consumption and distortion performance.

Separate Bias Voltage for each stage

Preamplifier, interstage attenuator, and driver amplifier have independent voltage supply pins.

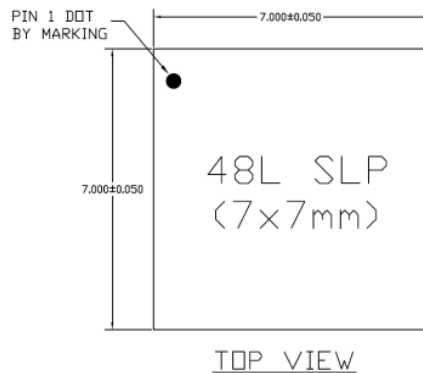
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Pin Description

Note: Pin numbers increment counter clockwise.



Pin	Symbol	Description
1, 6, 7, 8, 10, 11, 13, 15, 19, 26, 27, 28, 29, 31, 33, 34, 35, 36, 37, 38, 39, 42, 44, 45, 47, 48	NC	No Connect
2	RFIN1_P	PreAmp RF Input, Positive
3, 4	SRC1	PreAmp RF Source
5	RFIN1_N	PreAmp RF Input, Negative
9	RFOUT1_N	PreAmp RF Output, Negative
12	PD	Power Down Control
14	AGC	Current Based Attenuator Control
16, 17	VDDATT	Attenuator Bias
18	VG2_ADJ	Power Amplifier VG2 Bias Adjust
20, 25	VPA	Power Amplifier Supply
21	RFOUT2_N	Power Amplifier RF Output, Negative
22, 23, 43	GND	Ground Pin
24	RFOUT2_P	Power Amplifier RF Output, Positive
30	RFIN2_P	Power Amplifier RF Input, Positive
32	RFIN2_N	Power Amplifier RF Input, Negative
40	RFOUT_ATT_N	Attenuator RF Output, Negative
41	RFOUT_ATT_P	Attenuator RF Output, Positive
46	RFOUT1_P	PreAmp RF Output, Positive
49	GND	Backside Ground Slug

Pin DC Specifications

Pin	Symbol	Parameter	Min	Typ	Max	Units
12	PD	Input High Voltage	1.8			V
		Input Low Voltage			0.5	V
		Input High Current			300	uA
		Input Low Current			-50	uA
14	AGC	Input Current	-40		-1	mA

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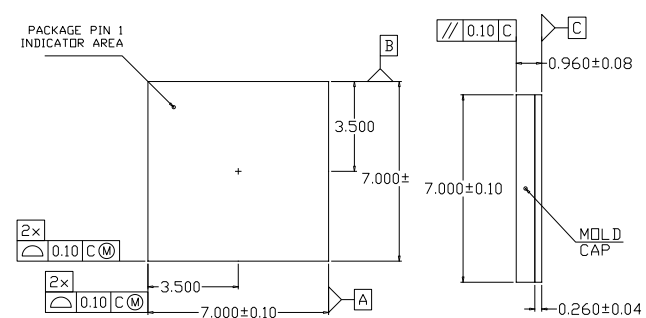
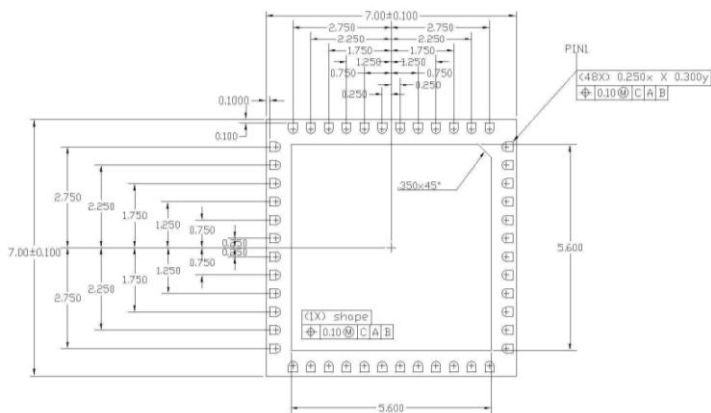


Mechanical Information

Package Information and Dimensions

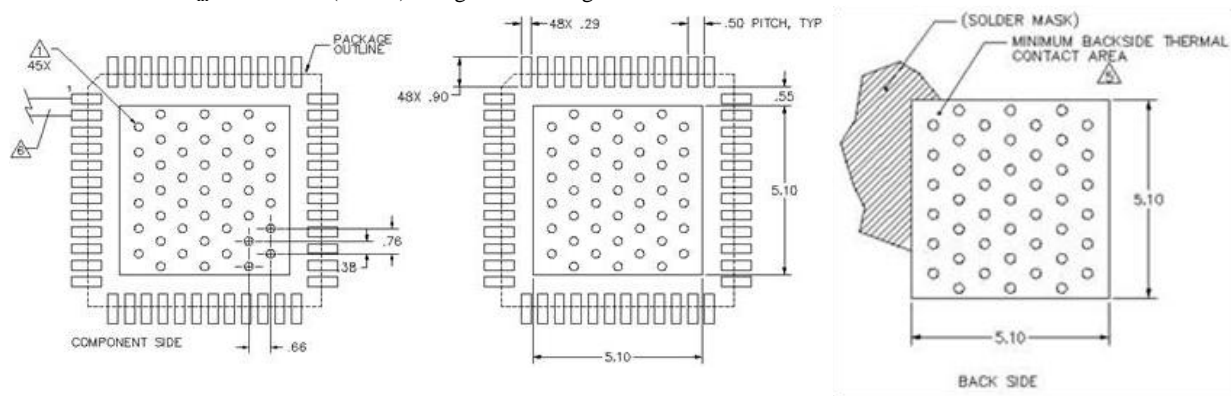
This package is lead-free/RoHS-compliant. The plating material on the leads is 100 % Matte Tin. It is compatible with both lead-free (maximum 260 °C reflow temperature) and lead (maximum 245 °C reflow temperature) soldering processes.

The TAT2814A will be marked with a “TAT2814A” designator and an 8 digit alphanumeric lot code (YYWWCCCC). The first four digits are a date code consisting of the year and work week (YYWW) of assembly. The last four digits are the lot code (XXXX).



Mounting Configuration

All dimensions are in millimeters (inches). Angles are in degrees.



Notes:

1. Ground / thermal vias are critical for the proper performance of this device. Vias should use a .35mm (#80/.0135”) diameter drill and have a final, plated thru diameter of .25 mm (.010”).
2. Add as much copper as possible to inner and outer layers near the part to ensure optimal thermal performance.
3. RF trace width depends upon the PC board material and construction.
4. All dimensions are in millimeters (inches). Angles are in degrees.

Product Compliance Information

ESD Information



Caution! ESD-Sensitive Device

ESD Rating:

Value:

Test: Human Body Model (HBM)

Standard: JEDEC Standard JESD22-A114

ESD Rating:

Value:

Test: Charged Device Model (CDM)

Standard: JEDEC Standard JESD22-C101

Solderability

Compatible with the latest version of J-STD-020, Lead free solder, 260°

This part is compliant with EU 2002/95/EC RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment).

MSL Rating

Level 3 at +260 °C convection reflow

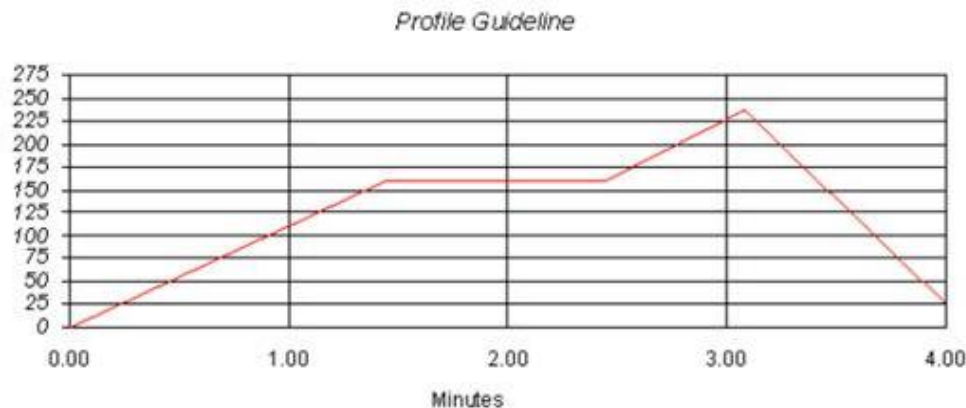
The part is rated Moisture Sensitivity Level 3 at 260°C per JEDEC standard IPC/JEDEC J-STD-020.

Recommended Soldering Temperature Profile

Solder paste manufacturers will recommend a "typical" solder reflow profile depending on their particular solder paste's flux and metal composition. This typical profile entails the parameters necessary for the solder to properly melt and reflow, and defines the thermal condition of the PCB soldering surface to be within an optimum temperature range. The recommended typical profile is obtained by mounting a thermo couple directly to the solder surface area of the PCB, and recording the actual local surface temperature during the reflow process.

The "oven profile" to achieve the "solder reflow profile" will be quite different. Oven profiles vary widely depending on reflow equipment, PCB, components loaded on the PCB, and other factors such as fixturing etc.

The following solder reflow profile is for a typical SAC305 no-lead solder paste application and assumes that standard PCB layout rules have been followed, such as solder mask to dam in molten solder during reflow to keep it from wicking away from the solder joint.



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Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations, and information about TriQuint:

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